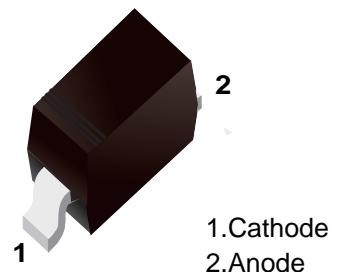


## ■ Schottky Barrier Diode

### ■ FEATURES

- Low Forward Voltage Drop.
- Guard Ring Construction For Transient Protection.
- Negligible Reverse Recovery Time.
- Low Reverse Capacitance.



■ Simplified outline(SOD-323)

### APPLICATIONS

- Schottky barrier switching.

Top View



### ■ MAXIMUM RATING @ Ta=25°C unless otherwise specified

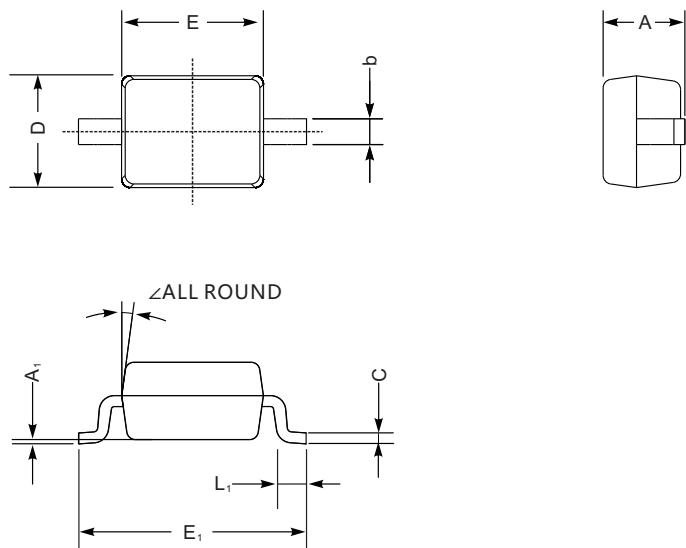
Parameter	Symbol	SD103AWS	SD103BWS	SD103CWS	Unit
Peak Repetitive Peak reverse voltage	V <sub>RR</sub>				
Working Peak DC Reverse Voltage	V <sub>RWM</sub>	40	30	20	V
RMS Reverse Voltage	V <sub>R(RMS)</sub>	28	21	14	V
Forward Continuous Current	I <sub>F</sub>		350		mA
Repetitive Peak Forward Current @t≤1.0s	I <sub>FRM</sub>		1.5		A
Power Dissipation	P <sub>d</sub>		400		mW
Thermal Resistance Junction to Ambient	R <sub>θjA</sub>		300		°C/W
Storage temperature	T <sub>stg</sub>		-65~+125		°C

### ■ ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage SD103AWS	V <sub>(BR)R</sub>	40			V	I <sub>R</sub> =10μA
SD103BWS		30				I <sub>R</sub> =10μA
SD103CWS		20				I <sub>R</sub> =10μA
Forward voltage	V <sub>F</sub>			0.37 0.60	V	I <sub>F</sub> =20mA I <sub>F</sub> =200mA
Reverse current SD103AWS	I <sub>RM</sub>			5.0	μA	V <sub>R</sub> =30V
SD103BWS						V <sub>R</sub> =20V
SD103CWS						V <sub>R</sub> =10V
Capacitance between terminals	C <sub>T</sub>		50		pF	V <sub>R</sub> =0,f=1MHz
Reverse Recovery Time	t <sub>rr</sub>		10		ns	I <sub>R</sub> =I <sub>F</sub> =200mA I <sub>rr</sub> =0.1*I <sub>R</sub> ,R <sub>L</sub> =100Ω

### ■ Marking

NO.	SD103AWS	SD103BWS	SD103CWS
Marking	S4	S5	S6

**■ SOD-323**

SOD-323 mechanical data

UNIT		A	C	D	E	E <sub>1</sub>	b	L <sub>1</sub>	A <sub>1</sub>	<
mm	max	1.1	0.15	1.4	1.8	2.75	0.4	0.45	0.2	9°
	min	0.8	0.08	1.2	1.4	2.55	0.25	0.2	—	
mil	max	43	5.9	55	70	108	16	16	8	9°
	min	32	3.1	47	63	100	9.8	7.9	—	

**■ The recommended mounting pad size**